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Kind regards,

Team Nexperia



PBHV8118T

180 V, 1 A NPN high-voltage low V_{CEsat} (BISS) transistor

Rev. 01 — 7 May 2010 Product data

Product data sheet

Product profile

1.1 General description

NPN high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

1.2 Features and benefits

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- AEC-Q101 qualified
- Small SMD plastic package

1.3 Applications

- LED driver for LED chain module
- LCD backlighting
- Automotive power management
- Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	180	V
I _C	collector current		-	-	1	Α
h _{FE}	DC current gain	$V_{CE} = 10 \text{ V};$ $I_{C} = 50 \text{ mA}$	[<u>1]</u> 100	250	-	

^[1] Pulse test: $t_D \le 300 \ \mu s; \ \delta \le 0.02$.



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2. Pinning information

Table 2. Pinning

Table 2.	Filling		
Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter	3	3
3	collector	1 2	1 — 2
			sym021

3. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBHV8118T	-	plastic surface-mounted package; 3 leads	SOT23		

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PBHV8118T	LZ*

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

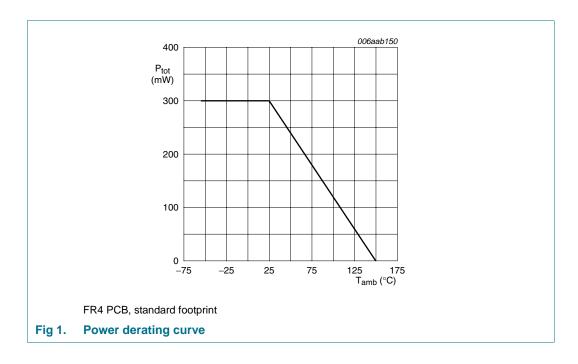
180 V, 1 A NPN high-voltage low V_{CEsat} (BISS) transistor

5. Limiting values

Table 5. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	400	V
V_{CEO}	collector-emitter voltage	open base	-	180	V
V_{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current		-	1	Α
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	2	Α
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	400	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	<u>[1]</u> -	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		–55	+150	°C
T_{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



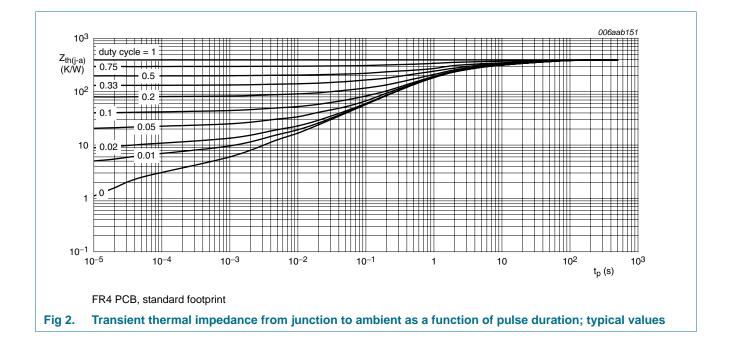
180 V, 1 A NPN high-voltage low V_{CEsat} (BISS) transistor

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1] -	-	417	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		-	-	70	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



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7. Characteristics

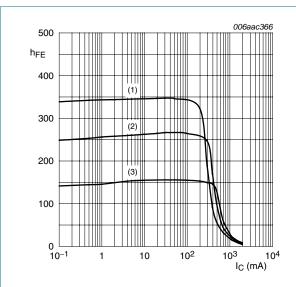
Table 7. Characteristics

 $T_{amb} = 25 \, ^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = 144 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nΑ
	current	$V_{CB} = 144 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$	-	-	10	μΑ
I _{CES}	collector-emitter cut-off current	$V_{CE} = 144 \text{ V}; V_{BE} = 0 \text{ V}$	-	-	100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = 4 \text{ V}; I_{C} = 0 \text{ A}$	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V	<u>[1]</u>			
		$I_C = 50 \text{ mA}$	100	250	-	
		$I_C = 100 \text{ mA}$	100	250	-	
		$I_C = 0.5 A$	50	100	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 100 \text{ mA}; I_B = 10 \text{ mA}$	[1] -	40	60	mV
		$I_C = 100 \text{ mA}; I_B = 20 \text{ mA}$	[1] -	33	50	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 0.5 \text{ A}; I_B = 100 \text{ mA}$	[1] -	1	1.2	V
t _d	delay time	$V_{CC} = 6 \text{ V}; I_{C} = 0.5 \text{ A};$	-	7	-	ns
t _r	rise time	$I_{Bon} = 0.1 \text{ A}; I_{Boff} = -0.1 \text{ A}$	-	565	-	ns
t _{on}	turn-on time		-	572	-	ns
t _s	storage time		-	1320	-	ns
t _f	fall time		-	740	-	ns
t _{off}	turn-off time		-	2060	-	ns
f_{T}	transition frequency	$V_{CE} = 10 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz	-	30	-	MHz
C _c	collector capacitance	$V_{CB} = 20 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	5.7	-	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = i_c = 0 \text{ A};$ f = 1 MHz	-	150	-	pF

^[1] Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

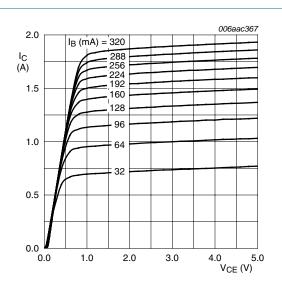
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$$V_{CE} = 10 \text{ V}$$

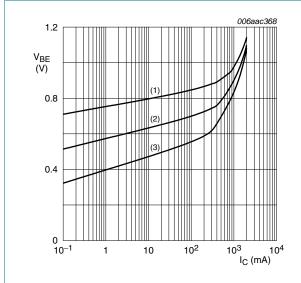
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 3. DC current gain as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

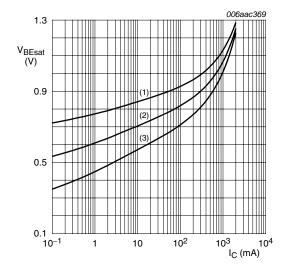
Fig 4. Collector current as a function of collector-emitter voltage; typical values



$$V_{CE} = 10 \text{ V}$$

- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 5. Base-emitter voltage as a function of collector current; typical values

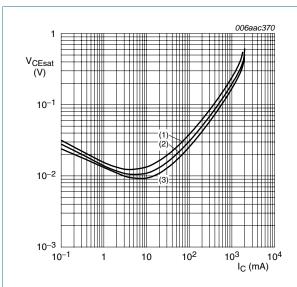


 $I_{\rm C}/I_{\rm B}=5$

- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Fig 6. Base-emitter saturation voltage as a function of collector current; typical values

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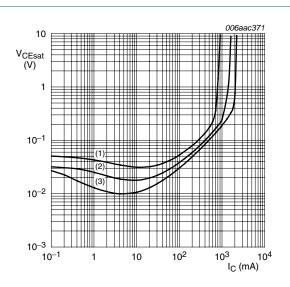
$$I_{\rm C}/I_{\rm B}=5$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



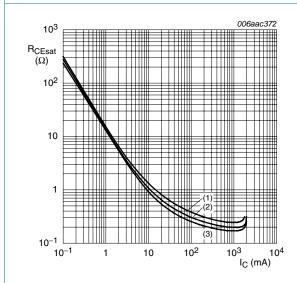
$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$I_C/I_B = 20$$

(2)
$$I_C/I_B = 10$$

(3)
$$I_C/I_B = 5$$

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values



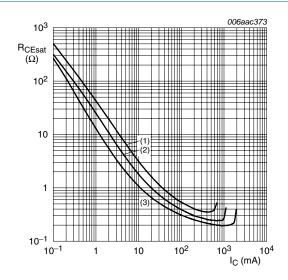
$$I_{\rm C}/I_{\rm B}=5$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 9. Collector-emitter saturation resistance as a function of collector current; typical values



(1)
$$I_C/I_B = 20$$

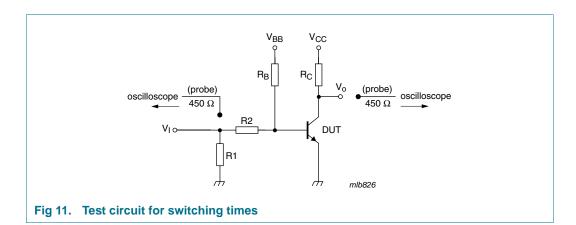
(2)
$$I_C/I_B = 10$$

(3)
$$I_C/I_B = 5$$

Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values

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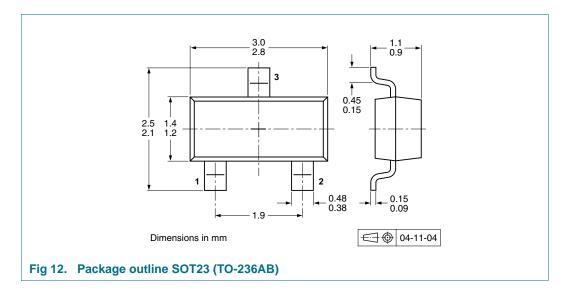
8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PBHV8118T	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

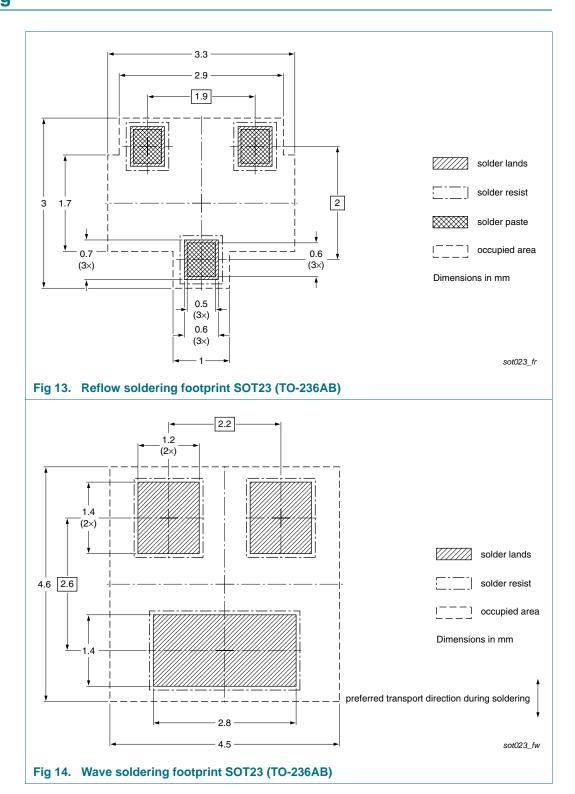
^[1] For further information and the availability of packing methods, see Section 14.

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11. Soldering



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12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBHV8118T v.1	20100507	Product data sheet	-	-

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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180 V, 1 A NPN high-voltage low V_{CEsat} (BISS) transistor

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